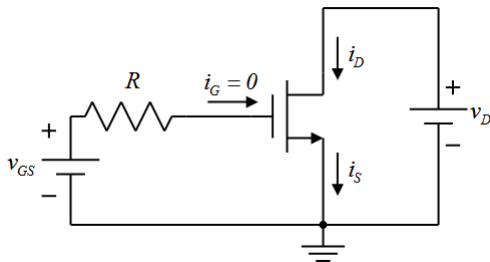


1. (6 points)

For the MOSFET in the circuit below $k'_n = \mu_n C_{ox} = 25 \frac{\mu A}{V^2}$, $W = 50 \mu m$, $L = 5 \mu m$, and $V_t = 3V$. Also $R = 1M\Omega$ and $v_{GS} = 4V$.

- Calculate i_D if $v_D = 0.5V$.
- Calculate i_D if $v_D = 8.7V$.

Note: In this problem, you may only submit numerical answers accurate to 0.02% or better. (i.e. If 4 is the correct answer, 3.9999 will be marked as correct, but 2+2 will be marked as incorrect.)



(a) i_D : ____ μA

(b) i_D : ____ μA

Correct Answers:

- 93.75
- 125

2. (6 points)

An N-MOSFET having $V_t = 1V$ is operated in the triode region with v_{DS} small. With $v_{GS} = 2.4V$ is found to have a resistance $r_{DS} = 970\Omega$.

- What value of V_{GS} is required to obtain $r_{DS} = 190\Omega$.
- With the previously computed value of V_{GS} , compute the resistance r_{DS} if the device W is doubled. .

Note: In this problem, you may only submit numerical answers accurate to 0.02% or better. (i.e. If 4 is the correct answer, 3.9999 will be marked as correct, but 2+2 will be marked as incorrect.)

(a) V_{GS} : ____ V

(b) r_{DS} : ____ Ω

Correct Answers:

- 8.14737
- 95

3. (6 points)

An N-MOSFET having $V_t = 1V$ and $k'_n(W/L) = 0.17 \frac{mA}{V^2}$ is operated in the saturation region.

- If i_D is to be $0.3mA$ find the required V_{GS} in volts.
- For the computed value of part a) find the minimum required v_{DS} in volts.

Note: In this problem, you may only submit numerical answers accurate to 0.02% or better. (i.e. If 4 is the correct answer, 3.9999 will be marked as correct, but 2+2 will be marked as incorrect.)

(a) v_{GS} : ____ V

(b) v_{DS} : ____ V

Correct Answers:

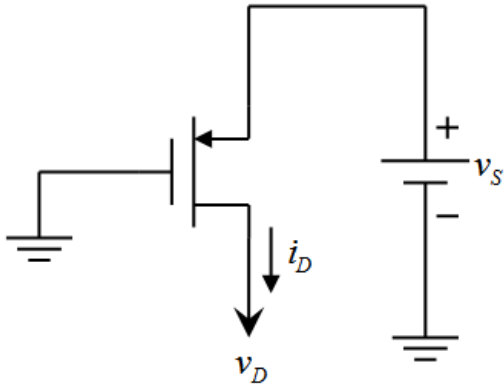
- 2.87867
- 1.87867

4. (6 points)

For the MOSFET in the circuit below $k'_p(W/L) = 80 \frac{\mu A}{V^2}$, $V_t = -1.5V$, and $\lambda = -0.02V^{-1}$. Also $v_S = 5V$.

- Calculate i_D if $v_D = 4.5V$.
- Calculate i_D if $v_D = -2.4V$.

Note: In this problem, you may only submit numerical answers accurate to 0.02% or better. (i.e. If 4 is the correct answer, 3.9999 will be marked as correct, but 2+2 will be marked as incorrect.)



(a) i_D : ____ μA

(b) i_D : ____ μA

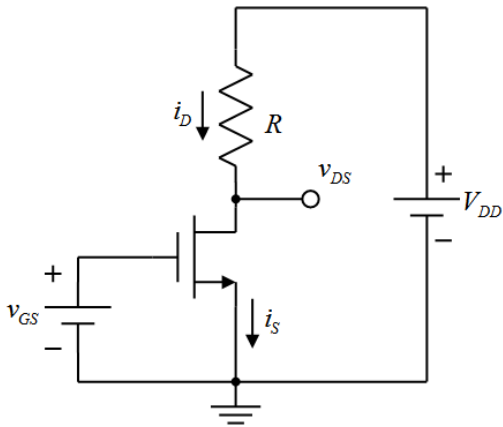
Correct Answers:

- 130
- 562.52

5. (6 points)

The MOSFET in the circuit shown is known to have a threshold voltage $0.9V \leq V_t \leq 3.1V$. Also $V_{DD}=15V$ and $R=710\Omega$. When $v_{GS}=4.1V$, $v_{DS}=14.89V$. When $v_{GS}=10V$, $v_{DS}=12.92V$. Find V_t . For this MOSFET $V_A = \infty$.

Note: In this problem, you may only submit numerical answers accurate to 0.02% or better. (i.e. If 4 is the correct answer, 3.9999 will be marked as correct, but 2+2 will be marked as incorrect.)



V_t : ____ V

Correct Answers:

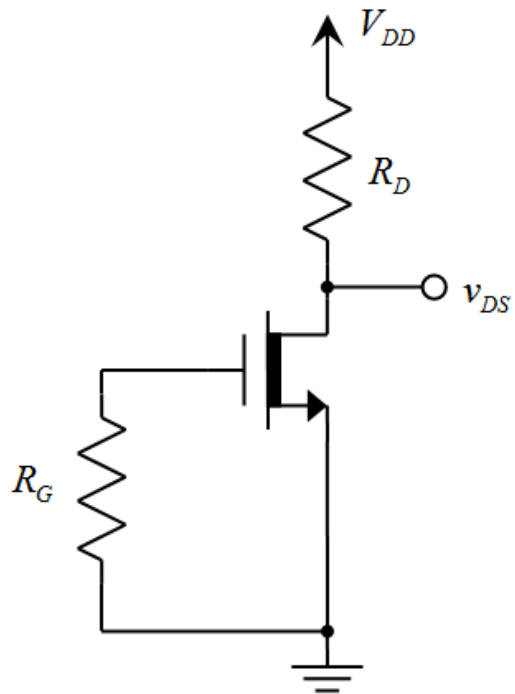
- 2.338

6. (10 points)

The MOSFET in the circuit shown is known to have a threshold voltage $V_t=-2V$ and $k'_n(W/L)=0.0001 \frac{A}{V^2}$. Also $V_{DD}=10V$.

- a. Compute i_D when $R_D=26300\Omega$ in μA .
- b. Compute v_{DS} when $R_D=26300\Omega$ in V.
- c. Compute i_D when $R_D=52000\Omega$ in μA .
- d. Compute v_{DS} when $R_D=52000\Omega$ in V.

Note: In this problem, you may only submit numerical answers accurate to 0.02% or better. (i.e. If 4 is the correct answer, 3.9999 will be marked as correct, but 2+2 will be marked as incorrect.)



a) i_D : ____ μA

b) v_{DS} : ____ V

c) i_D : ____ μA

d) v_{DS} : ____ V

Correct Answers:

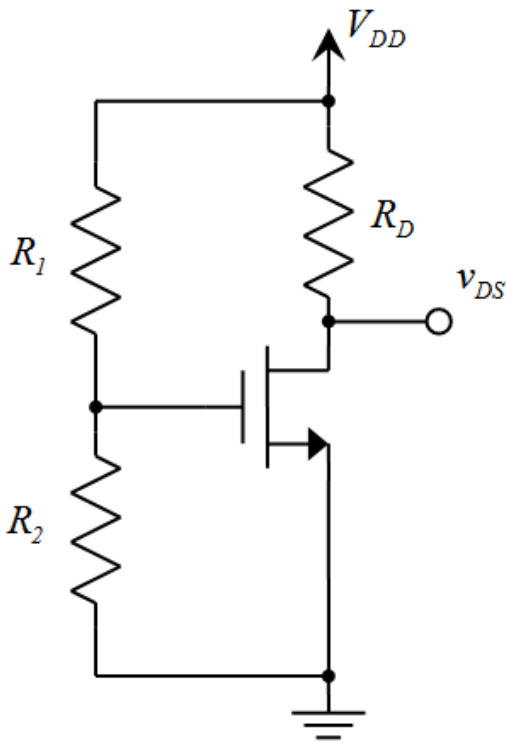
- 200
- 4.74
- 168.991
- 1.21248

7. (10 points)

The MOSFET in the circuit shown is known to have a threshold voltage $V_t=3\text{V}$, $k'_n(W/L)=0.1\frac{\text{mA}}{\text{V}^2}$, and $V_A = \infty$. Also $V_{DD}=12\text{V}$, $R_D=11600\Omega$, $R_1=2\text{M}\Omega$, and $R_2=4\text{M}\Omega$.

- Compute i_D in mA .
- Compute v_{DS} in V .

Note: In this problem, you may only submit numerical answers accurate to 0.02% or better. (i.e. If 4 is the correct answer, 3.9999 will be marked as correct, but 2+2 will be marked as incorrect.)



a) i_D : ____ mA

b) v_{DS} : ____ V

Correct Answers:

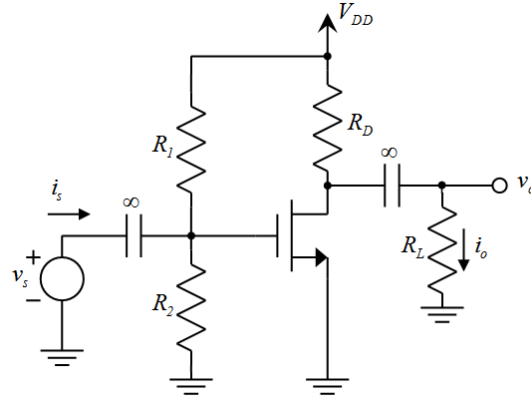
- 0.847913
- 2.16421

8. (12 points)

The MOSFET in the circuit shown is known to have a threshold voltage $V_t=2.5\text{V}$, $k'_n(W/L)=1\frac{\text{mA}}{\text{V}^2}$, and $V_A = \infty$. Also $V_{DD}=15\text{V}$, $R_D=12080\Omega$, $R_L=14300\Omega$, $R_1=3.1\text{M}\Omega$, and $R_2=1\text{M}\Omega$.

- Compute I_D in μA .
- Compute V_{DS} in V .
- Compute the voltage gain v_o/v_s

Note: In this problem, you may only submit numerical answers accurate to 0.02% or better. (i.e. If 4 is the correct answer, 3.9999 will be marked as correct, but 2+2 will be marked as incorrect.)



a) I_D : ____ μA

b) V_{DS} : ____ V

c) v_o/v_s : ____ V/V

Correct Answers:

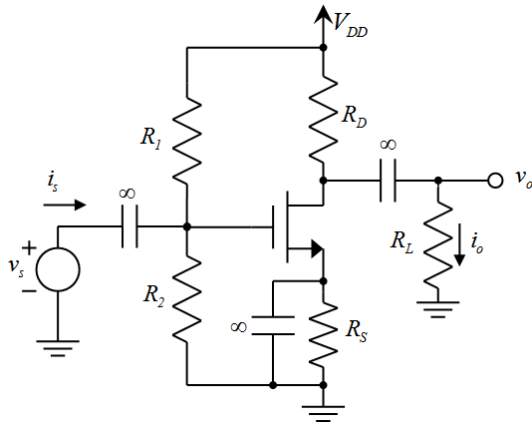
- 671.104
- 6.89307
- -7.58644

9. (12 points)

The MOSFET in the circuit shown is known to have a threshold voltage $V_t=1\text{V}$, $k'_n(W/L)=2\frac{\text{mA}}{\text{V}^2}$, and $V_A = \infty$. Also $V_{DD}=15\text{V}$, $R_D=7360\Omega$, $R_S=3480\Omega$, $R_L=10000\Omega$, $R_1=10\text{M}\Omega$, and $R_2=5\text{M}\Omega$.

- Compute I_D in μA .
- Compute V_{DS} in V .
- Compute the voltage gain v_o/v_s

Note: In this problem, you may only submit numerical answers accurate to 0.02% or better. (i.e. If 4 is the correct answer, 3.9999 will be marked as correct, but 2+2 will be marked as incorrect.)



- a) I_D : ____ μA
- b) V_{DS} : ____ V
- c) v_o/v_s : ____ V/V

Correct Answers:

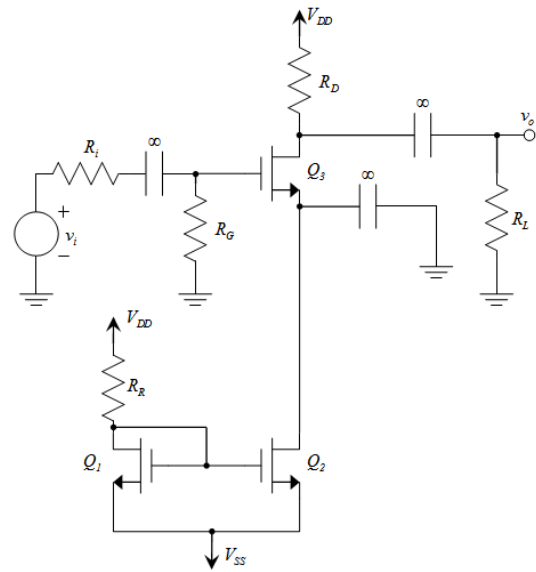
- 879.88
- 5.46211
- -7.95371

10. (16 points)

The MOSFETs in the circuit shown are all identical with a threshold voltage $V_t=2V$, $k'_n(W/L)=1 \frac{mA}{V^2}$, and $V_A=100V$. Also $V_{DD}=15V$, $V_{SS}=-15V$, $R_R=50600\Omega$, $R_D=14800\Omega$, $R_i=10000\Omega$, $R_L=10700\Omega$, and $R_G=5M\Omega$.

- Compute I_D in μA for Q3.
- Compute V_{DS} in V for Q3.
- Compute the voltage gain v_o/v_i

Note: In this problem, you may only submit numerical answers accurate to 0.02% or better. (i.e. If 4 is the correct answer, 3.9999 will be marked as correct, but 2+2 will be marked as incorrect.)



- a) I_D : ____ μA
- b) V_{DS} : ____ V
- c) v_o/v_i : ____ V/V

Correct Answers:

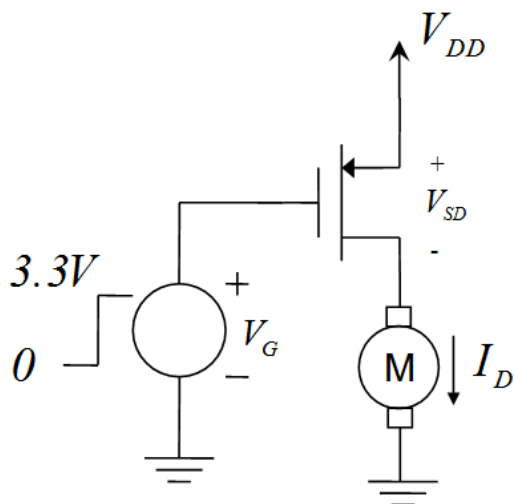
- 532.956
- 10.1447
- -6.1938

11. (5 points)

The MOSFET in the circuit shown has threshold voltage $V_t=2V$ and $r_{SD(on)}=0.27\Omega$. The motor can be represented in DC as a resistance $R_M=4.3\Omega$ and $V_{DD}=3.6V$.

- Compute I_D in mA when the MOSFET is "on".
- Compute V_{SD} in V when the MOSFET is "on".
- Compute the smallest possible motor resistance that will keep the MOSFET in the triode region in Ω .

Note: In this problem, you may only submit numerical answers accurate to 0.02% or better. (i.e. If 4 is the correct answer, 3.9999 will be marked as correct, but 2+2 will be marked as incorrect.)



a) I_D : ____ mA

b) V_{SD} : ____ V

c) R_M : ____ Ω

Correct Answers:

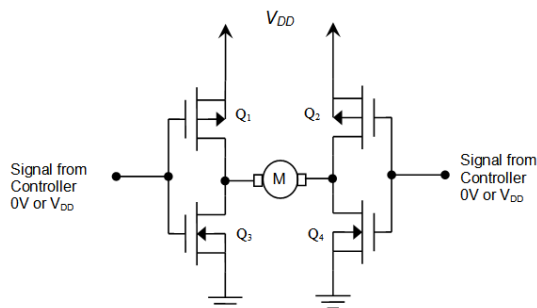
- 787.746
- 0.212691
- 0.3375

12. (5 points)

The N-MOSFETs in the circuit shown have threshold voltage $V_t=2V$ and $r_{DS(on)}=0.22\Omega$. The P-MOSFETs in the circuit shown have threshold voltage $V_t=3V$ and $r_{SD(on)}=0.25\Omega$. The motor can be represented in DC as a resistance $R_M=8.5\Omega$ and $V_{DD}=5.2V$.

- a. Compute the current motor in mA when it is turned on.
- b. Compute the maximum power dissipated by the N-MOSFETs in mW .
- c. Compute the maximum power dissipated by the P-MOSFETs in mW .

Note: In this problem, you may only submit numerical answers accurate to 0.02% or better. (i.e. If 4 is the correct answer, 3.9999 will be marked as correct, but 2+2 will be marked as incorrect.)



a) I_D : ____ mA

b) P_N : ____ mW

c) P_P : ____ mW

Correct Answers:

- 579.71
- 73.934
- 84.016